Keiko Masumoto

List of Publications by Year in descending order

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32 papers	187 citations	1305906 8 h-index	1336881 12 g-index
33 all docs	33 docs citations	33 times ranked	175 citing authors

#	Article	IF	Citations
1	Investigation of Factors Influencing the Occurrence of 3C-Inclusions for the Thick Growth of on-Axis C-Face 4H-SiC Epitaxial Layers. Materials, 2020, 13, 4818.	1.3	2
2	Reducing warpage of thick 4H-SiC epitaxial layers by grinding the back of the substrate. Japanese Journal of Applied Physics, 2019, 58, SBBD10.	0.8	1
3	Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, P547-P552.	0.9	1
4	Study of spiral growth on 4H-silicon carbide on-axis substrates. Journal of Crystal Growth, 2017, 475, 251-255.	0.7	5
5	Uniformity Improvement in Carrier Concentration on 150 mm Diameter C-Face Epitaxial Growth of 4H-SiC. Materials Science Forum, 2015, 821-823, 169-172.	0.3	4
6	Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1Â° off-angle. Japanese Journal of Applied Physics, 2015, 54, 04DP04.	0.8	7
7	Suppression of 3C-Inclusion Formation during Growth of 4H-SiC Si-Face Homoepitaxial Layers with a 1Â° Off-Angle. Materials, 2014, 7, 7010-7021.	1.3	7
8	Development of Homoepitaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate. Materials Science Forum, 2014, 778-780, 125-130.	0.3	2
9	Homo-Epitaxial Growth on 2Â° Off-Cut 4<i>H</i>-SiC(0001) Si-Face Substrates Using H₂-SiH₄-C₃H₈ CVD System. Materials Science Forum, 2014, 778-780, 214-217.	0.3	5
10	Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm Ï† Size SiC Epitaxial Wafer. Materials Science Forum, 2014, 778-780, 139-142.	0.3	0
11	Suppression of short step bunching generated on 4Hâ€“SiC Si-face substrates with vicinal off-angle. Journal of Crystal Growth, 2014, 401, 673-676.	0.7	9
12	Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 381, 139-143.	0.7	13
13	Reducing the Wafer Off Angle for 4H-SiC Homoepitaxy. ECS Transactions, 2013, 58, 111-117.	0.3	1
14	4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1Â°. ECS Journal of Solid State Science and Technology, 2013, 2, N3012-N3017.	0.9	16
15	The Effects of Substrate Surface Treatments on Growth of a-Plane GaN Single Crystals Using Na Flux Method. Japanese Journal of Applied Physics, 2012, 51, 035501.	0.8	2
16	The Effects of Ba-Additive on Growth of a-Plane GaN Single Crystals Using Na Flux Method. Japanese Journal of Applied Physics, 2012, 51, 040203.	0.8	8
17	Growth of Prismatic GaN Single Crystals with High Transparency on Small GaN Seed Crystals by Caâ€“Li-Added Na Flux Method. Applied Physics Express, 2012, 5, 025503.	1.1	20
18	Effect of additives on liquid phase epitaxy growth of nonâ€polar GaN single crystals using Na flux method. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 457-460.	0.8	9

#	Article	IF	Citations
19	Luminescence Characteristics and Annealing Effect of Tb-Doped AlBNO Films for Inorganic Electroluminescence Devices. Japanese Journal of Applied Physics, 2011, 50, 04DH01.	0.8	4
20	Influence of inserting AlN between AlSiON and 4Hâ€“SiC interface for the MIS structure. Applied Surface Science, 2011, 257, 8307-8310.	3.1	11
21	Luminescence Characteristics and Annealing Effect of Tb-Doped AlBNO Films for Inorganic Electroluminescence Devices. Japanese Journal of Applied Physics, 2011, 50, 04DH01.	0.8	3
22	Characterization of Si-added aluminum oxide (AlSiO) films for power devices. Applied Surface Science, 2010, 256, 1803-1806.	3.1	23
23	Annealing effect on photoluminescence of Tb-doped AlBON films. Solid State Communications, 2010, 150, 1396-1399.	0.9	4
24	Effect of nitrogen doping on the properties of AlSiO film for wide bandgap semiconductors. Applied Surface Science, 2010, 257, 1437-1440.	3.1	3
25	Characterization of Lanthanoid and Aluminum Based Oxide Film for Wide Bandgap Semiconductors. Materials Science Forum, 2010, 638-642, 3943-3948.	0.3	0
26	Synthesis and Characterization of Tb-doped AlBNO Films for Electroluminescence Devices. Materials Research Society Symposia Proceedings, 2009, 1195, 295.	0.1	0
27	Growth and properties of YAlO film synthesized by RF magnetron sputtering. Applied Surface Science, 2009, 255, 5021-5024.	3.1	1
28	The Growth of 3-Inch 4H-SiC Si-Face Epitaxial Wafer with Vicinal Off-Angle. Materials Science Forum, 0, 740-742, 193-196.	0.3	7
29	Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. Materials Science Forum, 0, 778-780, 99-102.	0.3	4
30	C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. Materials Science Forum, 0, 778-780, 109-112.	0.3	4
31	Influence of Epi-Layer Growth Pits on SiC Device Characteristics. Materials Science Forum, 0, 821-823, 177-180.	0.3	8
32	Improvement of 4H-SiC Epitaxial Layers Grown on 2<sup>o</sup> Offcut Si-Face Substrates. Materials Science Forum, 0, 858, 133-136.	0.3	2